

NTE586 Silicon Rectifier Diode Schottky Barrier, Fast Switching

Features:

- Low Switching Noise
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Capability

<u>Maximum Ratings and Electrical Characteristics:</u> $(T_A = +25^{\circ}C \text{ unless otherwise specified.}$ Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Ν | Maximum Recurrent Peak Reverse Current | 0V |
|---|---|-----|
| Ν | Maximum RMS Voltage | V8 |
| N | Maximum DC Blocking Voltage | 0V |
| N | Maximum Average Forward Rectified Current (375" . (9.5mm) lead length at T_L = +95°C) 3.0 | 0Α |
| F | Peak Forward Surge Current | |
| | (8.3ms single half sine–wave superimposed on rated load $T_L = +75^{\circ}C$) | 0Α |
| Ν | Maximum Instantaneous Forward Voltage at 3A DC (Note 1) | 5V |
| Ν | Maximum Average Reverse Current at Rated DC Blocking Voltage | |
| | $T_A = +25^{\circ}C$ | |
| | $T_A = +100^{\circ}C$ | nΑ |
| ٦ | rypical Thermal Resistance, Junction–to–Ambient (Note 2), R _{thJA} 80°C، | /W |
| ٦ | Typical Junction Capacitance (Note 3)110 | рF |
| (| Operating Junction Temperature Range T $_{ m J}$ $$ | 5°C |
| 5 | Storage Temperature Range T _{STG} | °C |
| | | |

- Note 1. measured at Pulse Width 300μs, Duty Cycle 2%.
- Note 2. Thermal Resistance Junction to Ambient Vertical PC Board Mounting, 0.5" (12.7mm) Lead Length.
- Note 3. Measured at 1MHz and applied reverse voltage of 4.0 Volts.

